TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOS)

TK80E08K3

■ E-Bike/UPS/Inverter

• Low drain–source ON resistance : $RDS (ON) = 7.5 \text{ m}\Omega \text{ (typ.)}$ • High forward transfer admittance : $|Y_{fs}| = 135 \text{ S (typ.)}$ • Low leakage current : $IDSS = 10 \text{ } \mu A \text{ (max)} \text{ (VDS} = 75 \text{ V)}$

• Enhancement mode : $V_{th} = 2.0 \sim 4.0 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1 \text{ mA})$

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	75	V	
Drain-gate voltage (R _{GS} = 20 kΩ)		V_{DGR}	75	V	
Gate-source voltage		V _{GSS}	±20	V	
Drain current	DC (Note 1)	ID	80	Α	
	DC (Note 1,4)	DC (Note 1,4) I _D 70		Α	
	Pulse (Note 1)	I _{DP}	240	Α	
Drain power dissipation (Tc = 25°C)		P _D	200	W	
Single pulse avalanche energy (Note 2)		E _{AS}	107	mJ	
Avalanche current		I _{AR}	40	Α	
Repetitive avalanche energy (Note 3)		E _{AR}	20	mJ	
Peak diode recovery dv/dt (Note 5)		dv/dt	12	V/ns	
Channel temperature (Note 4)		T _{ch}	175	°C	
Storage temperature range (Note 4)		T _{stg}	-55~175	°C	

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	0.75	°C / W
Thermal resistance, channel to ambient	R _{th (ch-a)}	83.3	°C / W

Note 1: Ensure that the channel temperature does not exceed 175°C.

Note 2: V_{DD} = 25 V, T_{ch} = 25°C (initial), L = 100 μ H, R_{G} = 25 Ω , I_{AR} = 40A

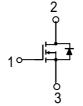
Note 3: Repetitive rating: pulse width limited by maximum channel temperature

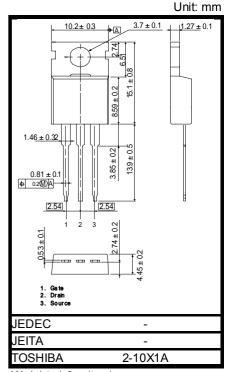
Note 4: Tc=100

Note 5: IDR 80A,di/dt 160A/µs, Tch Tch max.

This transistor is an electrostatic-sensitive device.

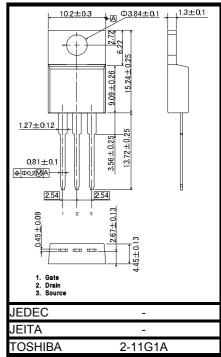
Please handle with caution.





Weight: 1.9 g (typ.)

Unit: mm



Weight: 1.9 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc). Thermal Characteristics

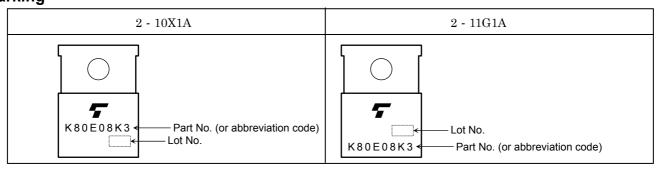
Electrical Characteristics (Ta = 25°C)

Charac	eteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	rrent	I _{GSS}	V _{GS} = ±20 V, V _{DS} = 0 V	_	_	±1	μΑ
Drain cut-off cui	rrent	I _{DSS}	V _{DS} = 75 V, V _{DS} = 0 V	_	_	10	μΑ
Drain-source br	eakdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	75	_	_	V
		V (BR) DSX	I _D = 10 mA, V _{GS} = -20 V	45	_		V
Gate threshold v	oltage	V_{th}	V _{DS} = 10 V, I _D = 1 mA	2.0	_	4.0	V
Drain-source Ol	N resistance	R _{DS} (ON)	V _{GS} = 10 V, I _D = 40 A	_	7.5	9.0	mΩ
Forward transfer	admittance	Y _{fs}	V _{DS} = 10 V, I _D = 40 A	67	135	_	S
Input capacitano	е	C _{iss}		_	3600	_	
Reverse transfer capacitance		C _{rss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	-	350	_	pF
Output capacitance		Coss	1		500	_	
Switching time	Rise time	t _r	$V_{GS} = 40 \text{ A} V_{OUT}$ $V_{GS} = 0.9 \Omega$	_	16	_	- ns
	Turn-on time	t _{on}		_	33	_	
	Fall time	t _f		_	13	-	
	Turn-off time	t _{off}	$V_{DD} \simeq 35 \text{ V}$ Duty \leq 1%, $t_W = 10 \text{ μs}$	_	63	_	
Total gate charge (Gate-source plus gate-drain)		Qg		_	75	_	
Gate-source charge		Q _{gs}	$V_{DD} \approx 60 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 80 \text{ A}$		44	_	nC -
Gate-drain ("miller") charge		Q _{gd}			31	_	

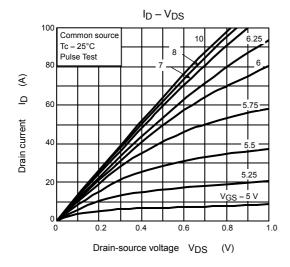
Source-Drain Ratings and Characteristics (Ta = 25°C)

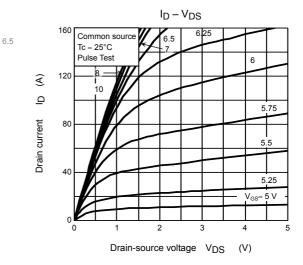
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	_	_	80	Α
Pulse drain reverse current (Note 1)	I _{DRP}	_	_	_	240	Α
Forward voltage (diode)	V_{DSF}	I _{DR} = 80 A, V _{GS} = 0 V	_	_	-1.5	V
Reverse recovery time	t _{rr}	I _{DR} = 80 A, V _{GS} = 0 V		45		ns
Reverse recovery charge	Q _{rr}	dl _{DR} / dt = 100 A / μs		72		μC

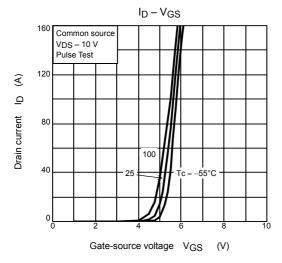
Marking

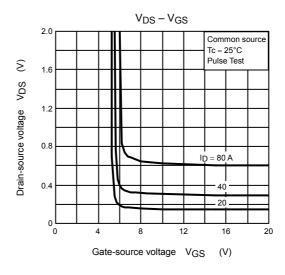


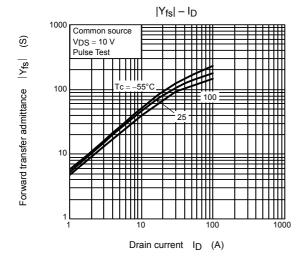
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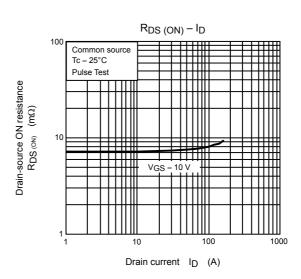




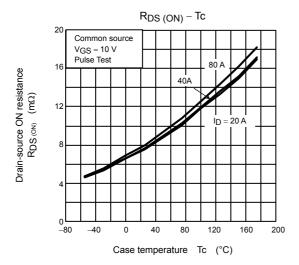


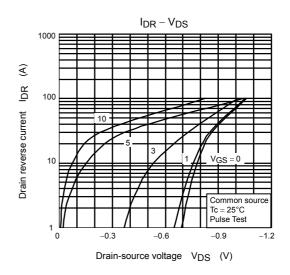


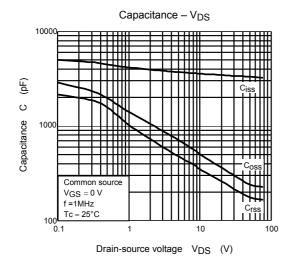


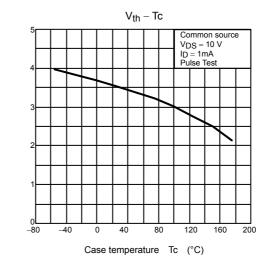


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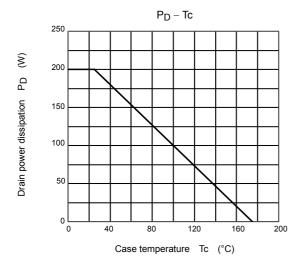
V_{th}

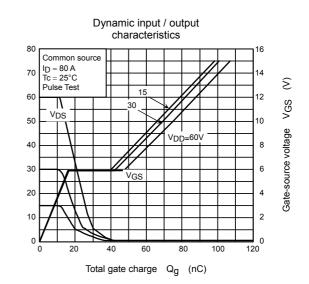
Gate threshold voltage

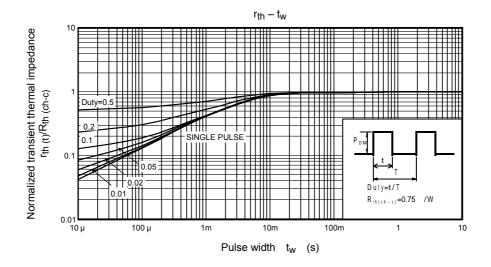
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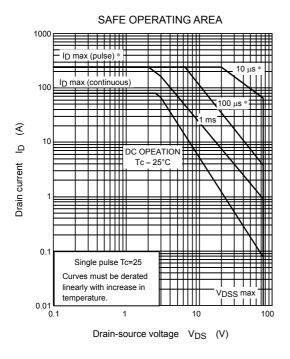
Drain-source voltage VDS

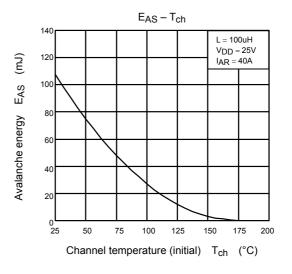
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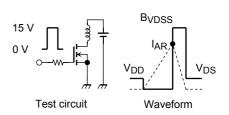












$$\begin{aligned} R_G &= 25~\Omega \\ V_{DD} &= 25~V,~L = 100~\mu H \end{aligned} \qquad E_{AS} &= \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right) \end{aligned}$$

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